

# HIREX ENGINEERING®

Radiation Evaluation of Commercial  
Off-The-Shelf (COTS)



Non-Volatile Memories (NVRAMs)

Contract N° 13528/99/NL/MV, COO-1

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J.F. PASCAL, F.X. GUERRE





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## Evaluation Content

- ▶ Parts Selection
- ▶ Total Ionizing Dose
- ▶ Single Event Effects





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## Outline Presentation

- ▶ Tested Products
- ▶ Total Ionizing Dose
- ▶ Single Event Effects





# Tested Products

## ➔ Non Volatile memories

- ➔ FRAM
- ➔ EEPROM
- ➔ Flash

## ➔ RAM memories





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## Total Ionizing Dose Evaluation





# TID Tested Products: Memories

Manufacturer	Type	Description
Ramtron	FM1808	32K x 8 FRAM
Atmel	AT28LV010	128K x 8 EEPROM
Xicor	X28C010	128K x 8 EEPROM
Hitachi	HN58C1001	128K x 8 EEPROM
Intel	E28F128J	16M x 8 Flash EPROM
Samsung	K9F2808U0M	16M x 8 Flash EPROM
IDT	IDT7025	8K x 16 DPRAM





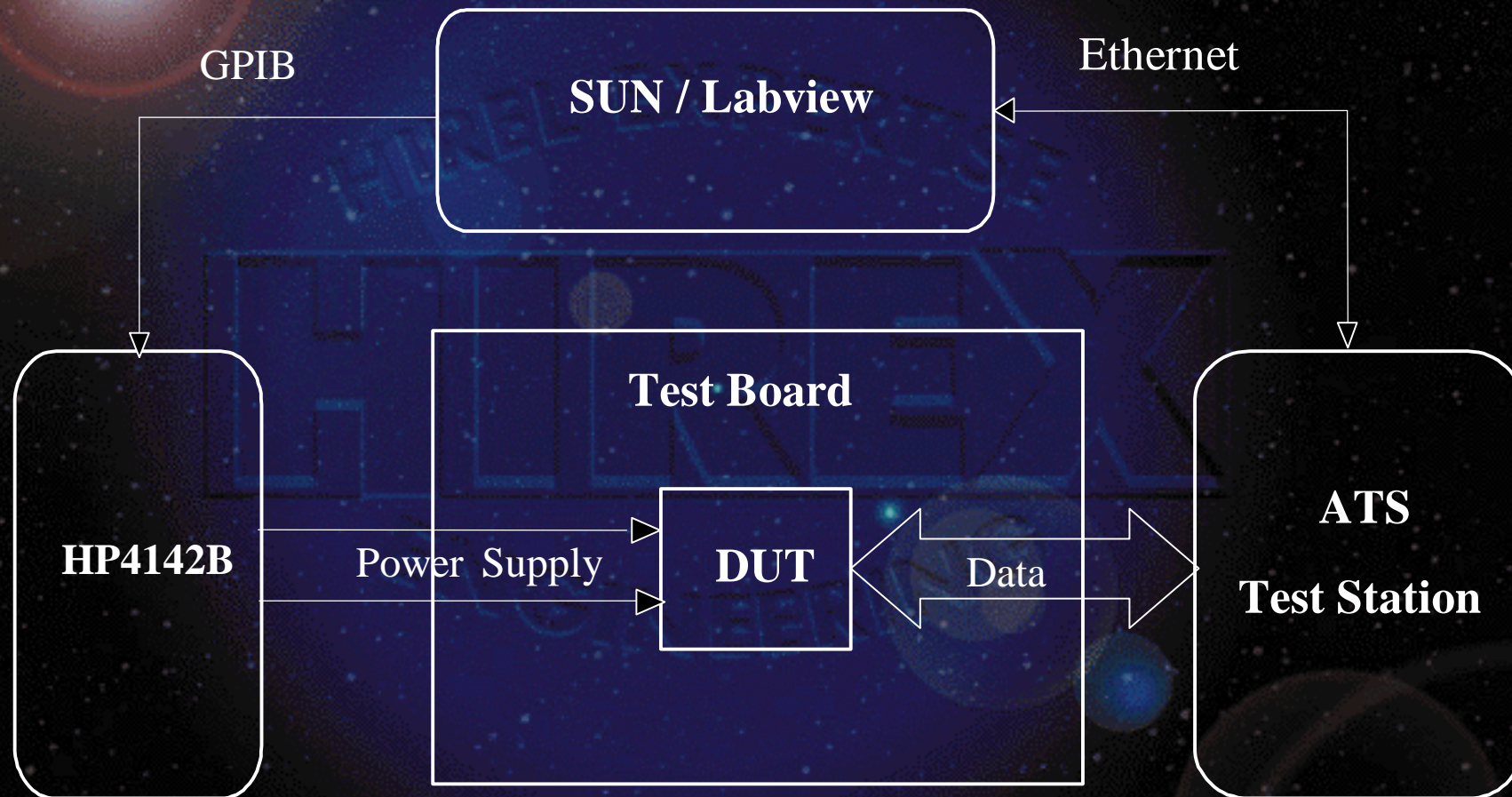
# TID Tested Electrical Parameters

- ➔ Input, Output Leakage currents ( $I_{il}$ ,  $I_{ih}$ ,  $I_{ozl}$ ,  $I_{ozh}$ ), Output Voltages ( $V_{oh}$ ,  $V_{ol}$ )
- ➔ Supply currents (Operating, Standby TTL, Standby CMOS)
- ➔ Functional test @ max speed, 4 patterns





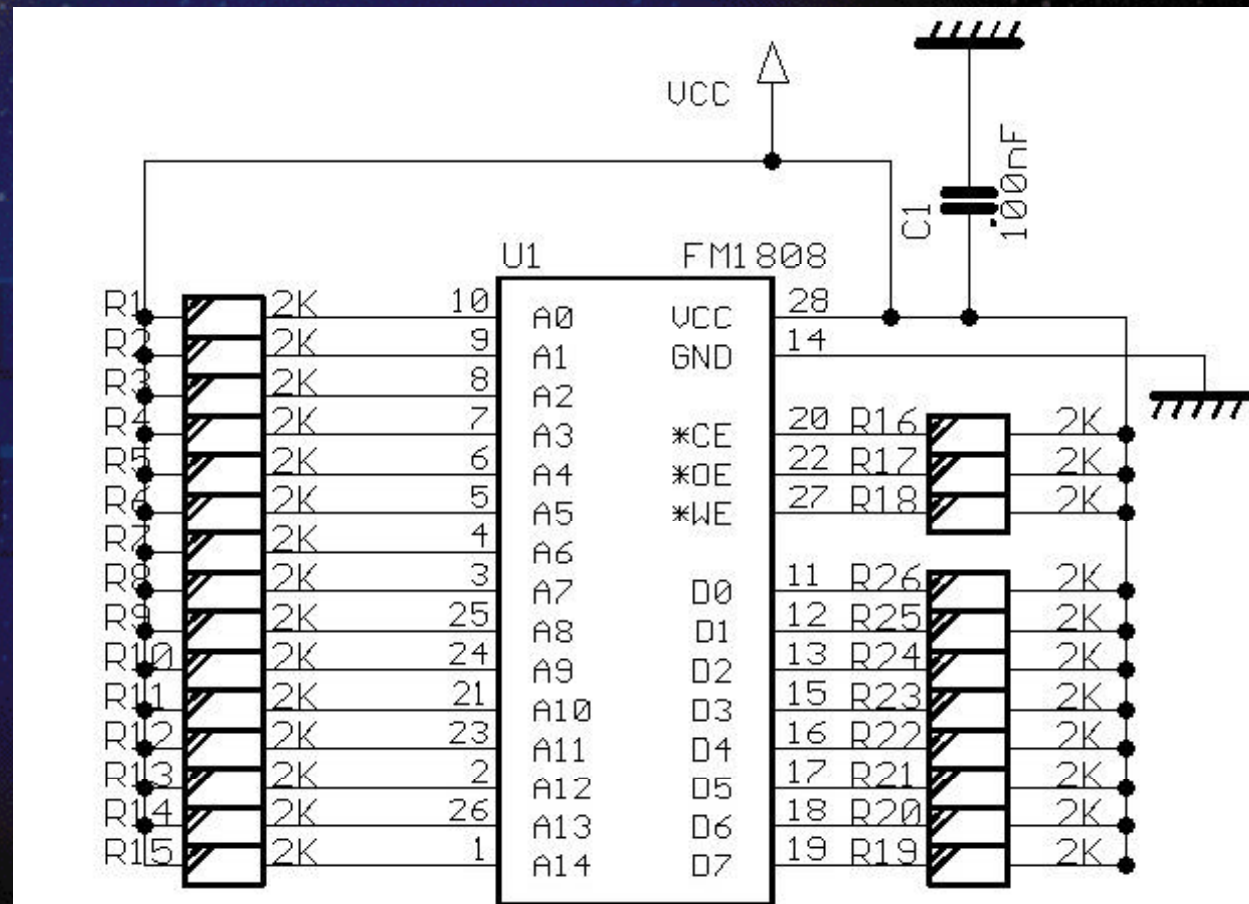
# TID Test Programs Principle





# TID Bias Conditions: FRAM

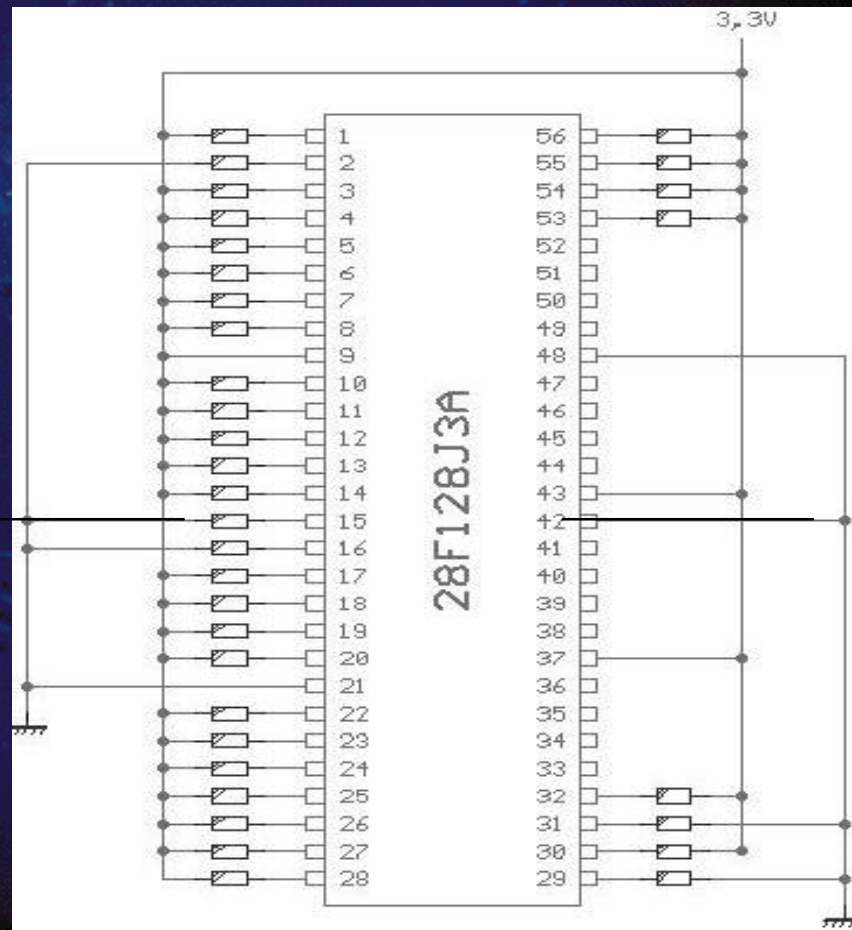
FM1808





# TID Bias Conditions: Flash

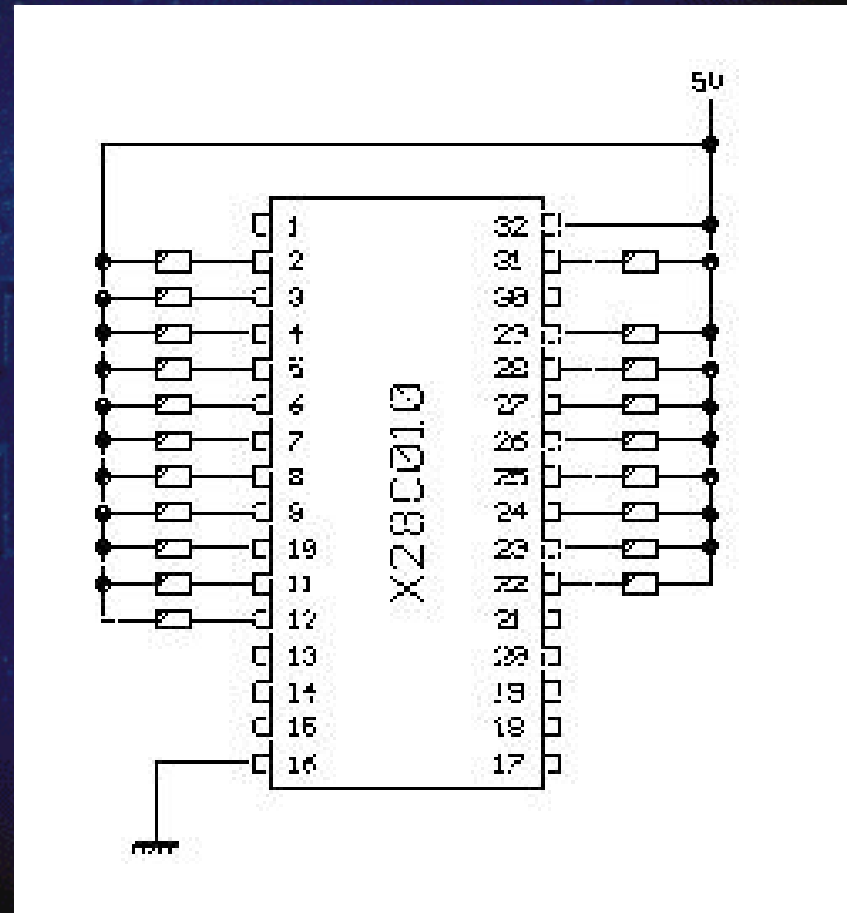
28F128J3A





# TID Bias Conditions: EEPROM

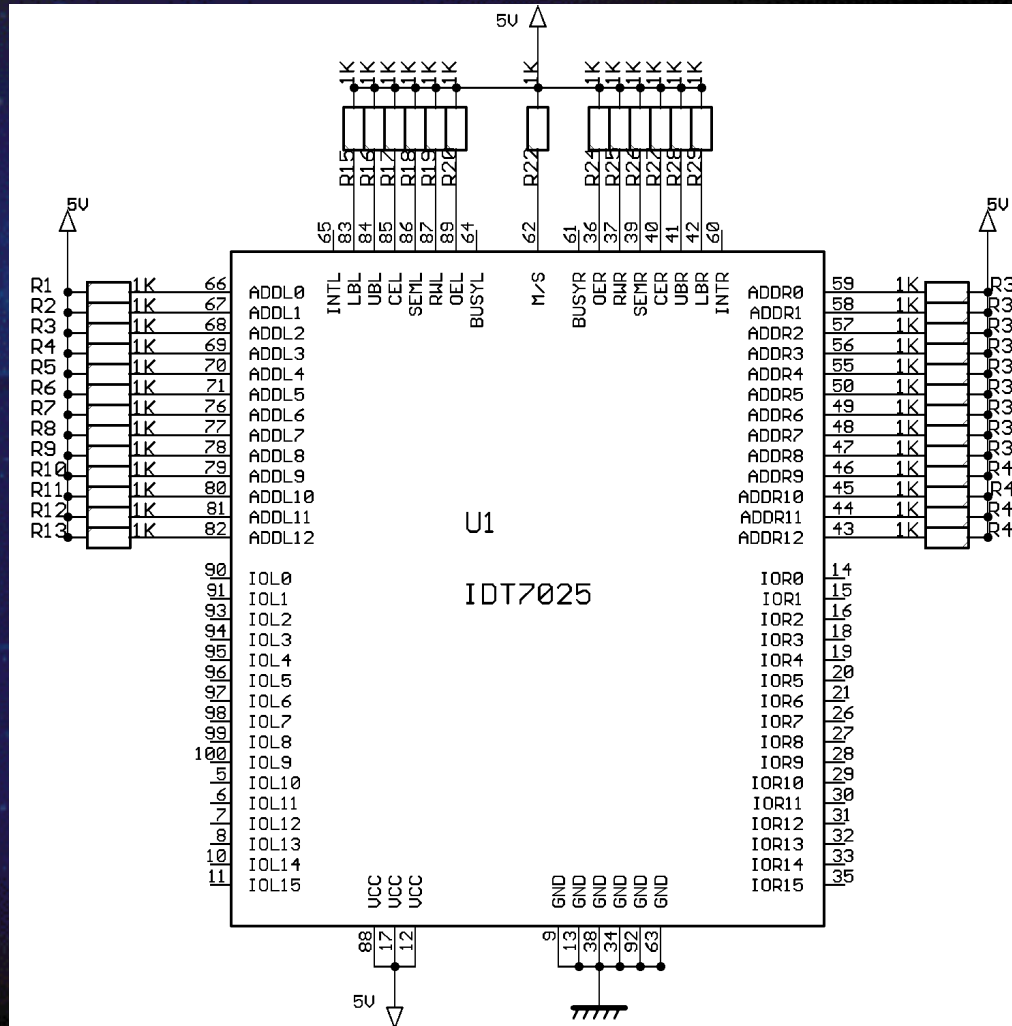
X28C010





# TID Bias Conditions: DPRAM

IDT7205





# TID Tests Conditions

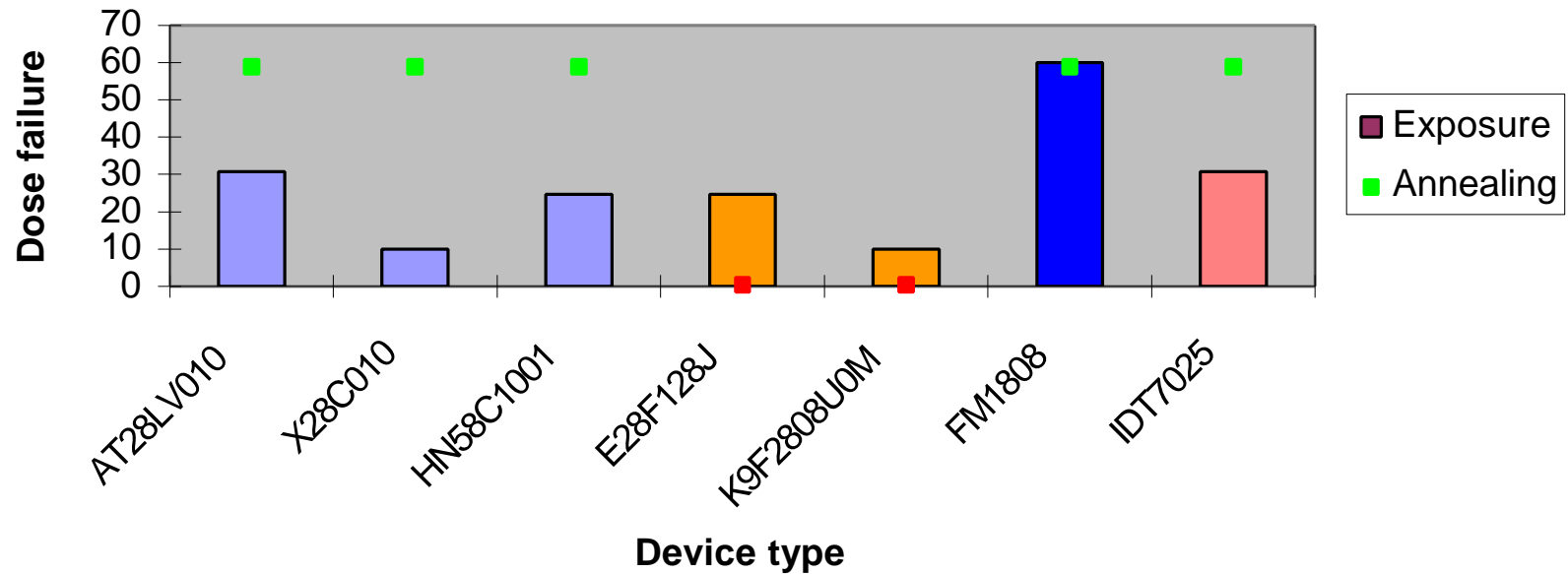
- ➔ 5 Samples per type tested
- ➔ Dose rate: 200 rad(Si)/hour
- ➔ Irradiation and testing at room temperature
- ➔ CO60 Exposures at ONERA up to 50-60 Krad(Si) in 5 or 6 steps
- ➔ Annealing: 24H at 25°C & 168H at 100°C





# TID Test Results: Functional

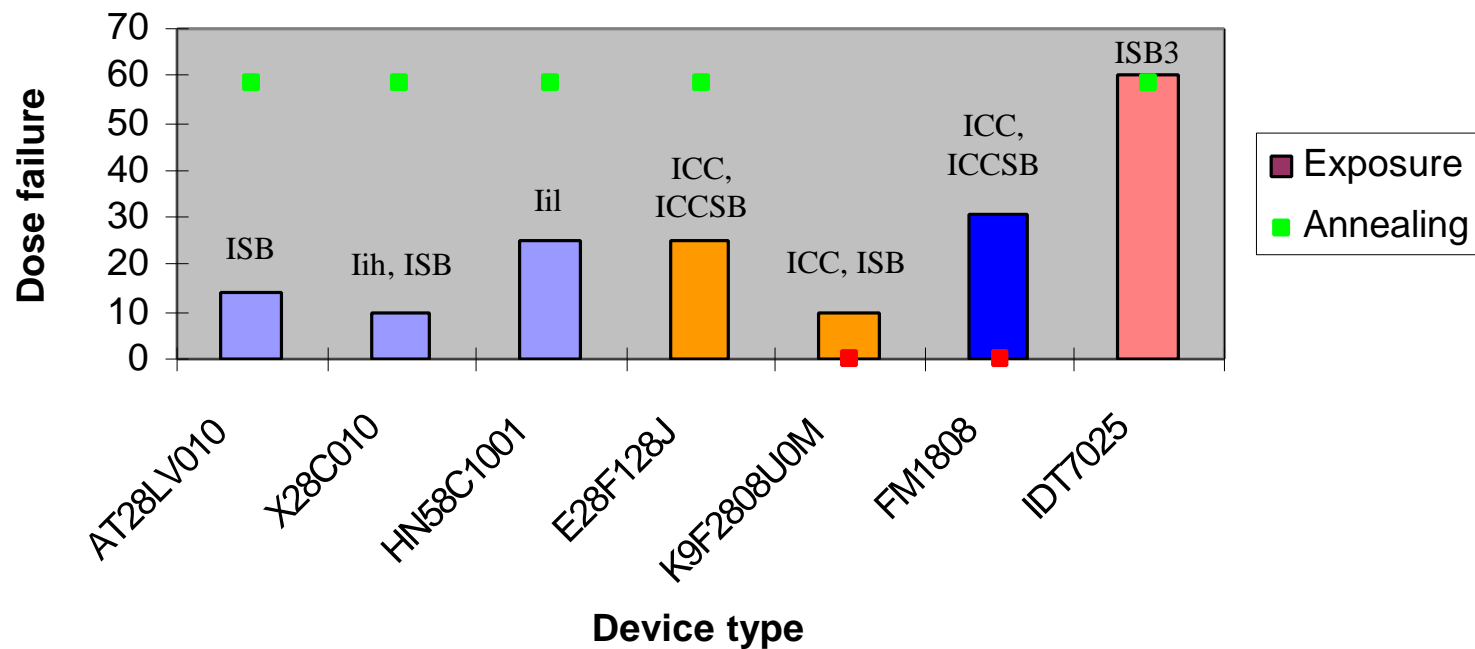
## Functional behaviour of memory devices





# TID Test Results: DC parameters

## DC parameters behaviour of memory devices





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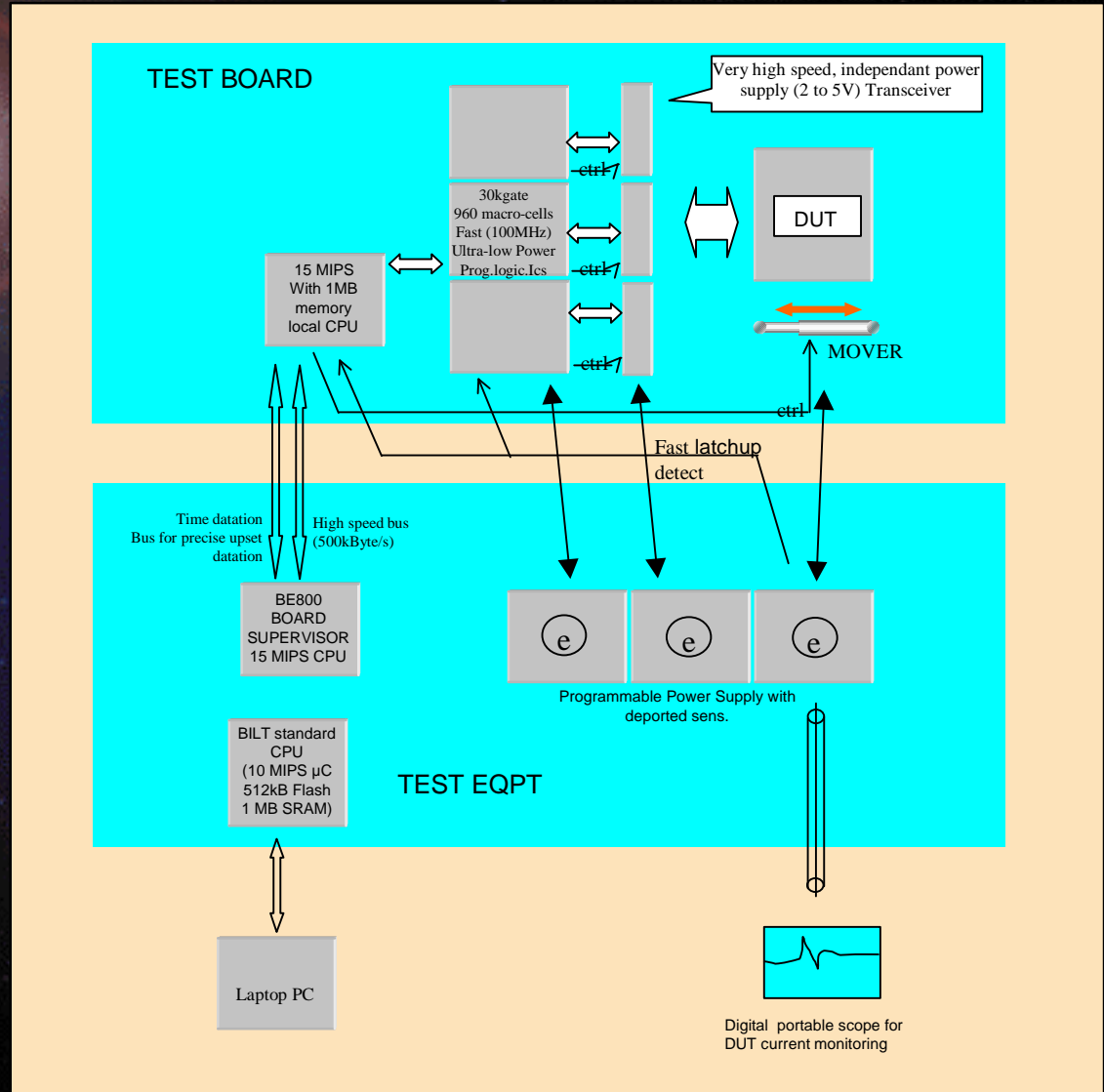
## Single Event Effect Evaluation of Non Volatile Memories (NVRAMs)



Test performed in April 00 and September 00,  
at the European Heavy Ion Facility (HIF),  
Université catholique de Louvain, (Belgium)









# NVRAM SEE Test Conditions

## Static mode : 1 cycle

- Write the memory not exposed to the beam
- Expose the DUT for the expected fluence
- Read the memory not exposed to the beam

## Read only mode: Repetitive cycles

- Write the memory not exposed to the beam
- Expose the DUT for the expected fluence
- Read the memory continuously

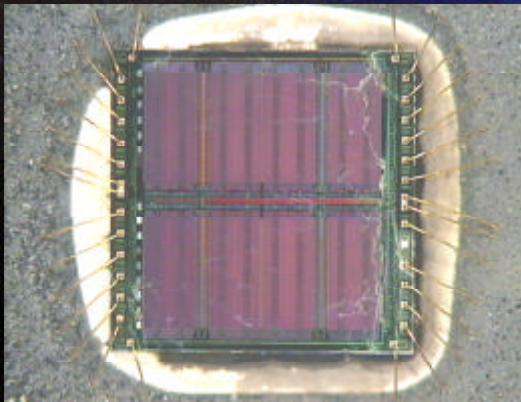
## Read / write mode: Repetitive cycles

- Write the memory not exposed to the beam
- Expose the DUT for the expected fluence
- Read/write the memory continuously





# FM1808 RAMTRON



- Ferro-electric Random Access Memory (FRAM)
- FM1808-120-P
- 28-pin plastic DIP
- 32k x 8
- 5V operation
- 180ns cycle time
- Ferro-electric process
- Die : 4.6 mm x 4.6 mm



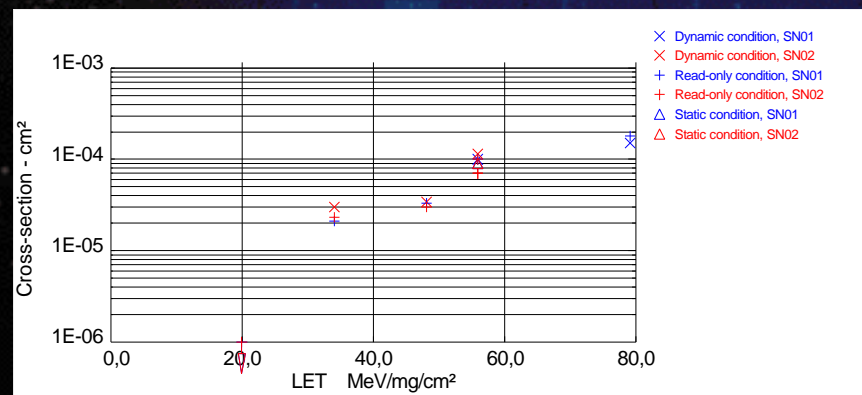
Non volatile but operates as a RAM  
for read and write





# FM1808 SEE RESULTS

- ➔ Not sensitive to SEU up to an LET of 80 MeV/(mg/cm<sup>2</sup>)
- ➔ Sensitive to SEL
- ➔ In static mode, SEL does not affect the memory content



## SEL Cross section

LET threshold between  
20 and 34 MEV/(mg/cm<sup>2</sup>)

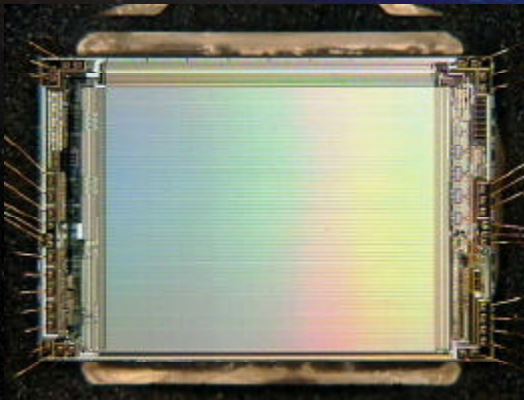
Asymptotic cross-section  
1.8 E- 4 cm<sup>2</sup>





# AT28LV010 ATMEL

- EEPROM
- AT28LV010-25PI
- 32-lead plastic DIP
- 128k x 8
- 3V3 operation
- 200ns Read Access Time
- 10ms max, Page Write Cycle Time
- CMOS
- Die : 9.2 mm x 6.2 mm



Internal error correction for improved data retention





# AT28LV010 SEE RESULTS

**Static mode :** Krypton(34)

➡ No SEU (tilt angle 0 deg.)

**Read only mode:** Neon(5.9), Argon (14), Krypton(34)

➡ No error Neon @ 60 deg

➡ 1st Functional error Argon @ 0 deg.

➡ No other type of error

**Read / write mode:** Neon(5.9), Argon (14), Krypton(34)

➡ 1st Functional error Neon @ 60 deg

➡ Few Page errors (128 bytes range)

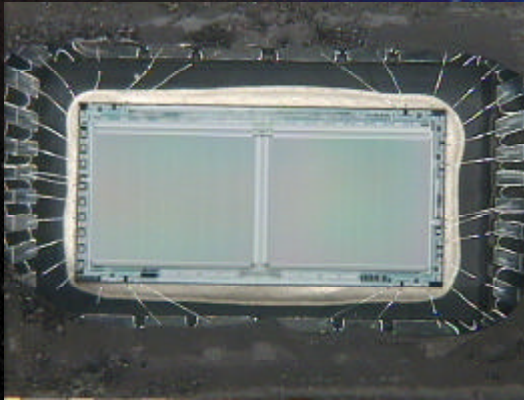
➡ No Single error (1 single random bit at a random address)





# X28C010 XICOR

- EEPROM
- X28C010D-12
- 32-lead CERDIP
- 128k x 8
- 5V operation
- 120ns Read Access Time
- 10ms max, Page Write Cycle Time
- CMOS
- Die : 12.7 mm x 6.2 mm





# X28C010 SEE RESULTS

## Static mode : Krypton(34)

➡ No SEU (tilt angle 0 deg.)

## Read only mode: Neon(5.9), Argon (14), Krypton(34)

➡ 1st half-page (128 bytes) error Neon @ 0 deg.

➡ Few MEUs, > 1 bit at a random address, Neon @ 0 deg.

➡ 1st functional error Argon @ 0 deg.

## Read / write mode: Neon(5.9), Argon (14), Krypton(34)

➡ Same behaviour as read only mode

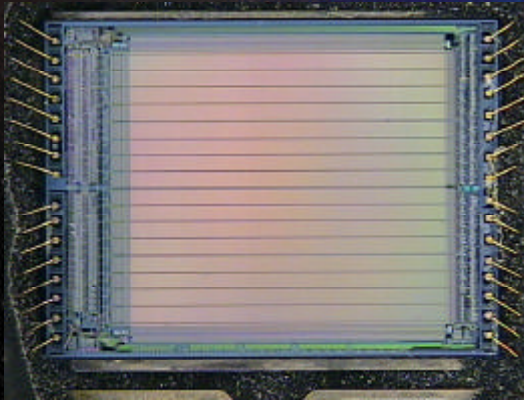
➡ Single errors, 1 bit at a random address Neon @ 0. deg.





# HN58C1001 HITACHI

- EEPROM
- HN58C1001FP-15
- 32-pin plastic SOP
- 128k x 8
- 5V operation
- 150ns Read Access Time
- 10ms max, Page Write Cycle Time
- MNOS (memory cells),CMOS (Logic)
- Die : 8.3 mm x 6.2 mm





# HN58C1001 SEE RESULTS

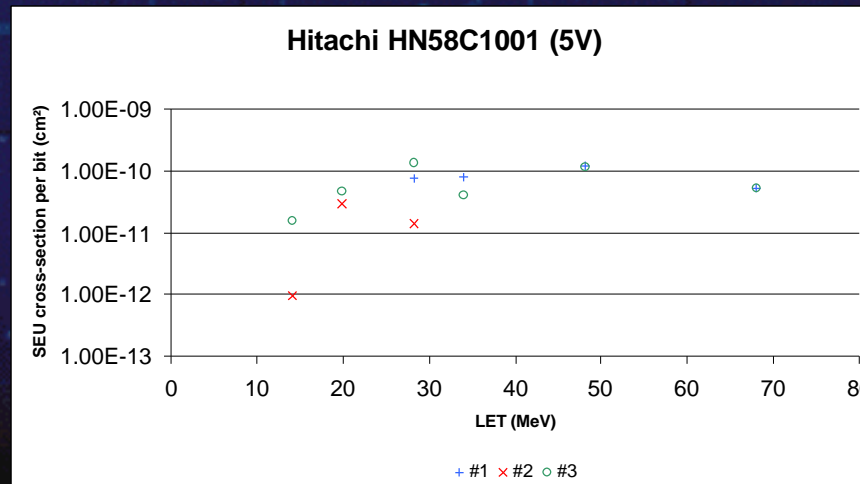
**Read only mode:** Argon (14), Krypton(34)

➡ No error Krypton @ 60 deg. (68)

**Read / write mode:** Argon (14), Krypton(34)

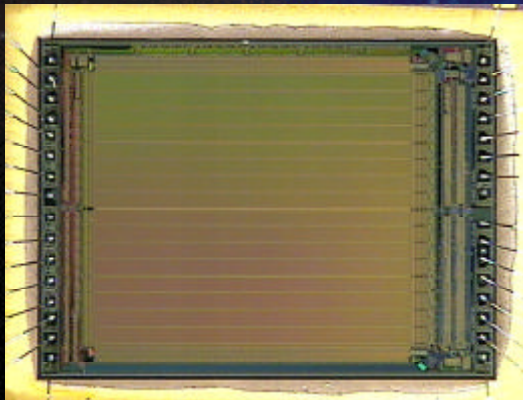
➡ 1st Page (128 bytes) error Krypton @ 0 deg.

➡ Single errors, 1 bit at a random address Argon @ 0. deg.





# MEM8129 HMP



- EEPROM
- MEM8129JMB-15
- Ceramic JLCC
- 128k x 8
- 5V operation
- 150ns Read Access Time
- 10ms max, Page Write Cycle Time
- MNOS (memory cells),CMOS (Logic)
- Die : 8.3 mm x 6.2 mm



Hitachi die 58C1001





# MEM8129 SEE RESULTS

➔ **Static mode** : Krypton(34)

➔ No SEU (tilt angle 0 deg.)

➔ **Read only mode**: Argon (14), Krypton(34)

➔ No error Krypton @ 0 deg.

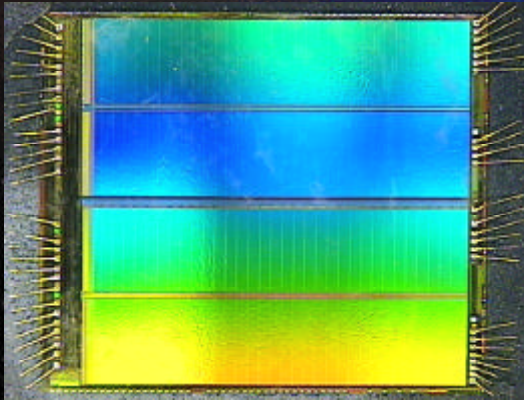
➔ **Read / write mode**: Argon (14), Krypton(34)

➔ Permanent error Krypton @ 0deg.  
2 samples, stuck bits in a page  
Partial recovery over time (hours)





# 28F128J INTEL



- Flash
- E28F128J3A150
- 56-lead TSOP
- 128Mbit (128 blocks of 128kbytes)
- 3V operation
- 150ns Read Access Time
- 1.0 s min Block Erase Time
- 0.25 $\mu$  ETOX VI Intel Process
- Die : 10.5 mm x 8.9 mm



Intel StrataFlash means 2-bit-per-cell technology





# 28F128J SEE RESULTS

## Static mode : Argon (14)

- ➔ SEU sensitive
- ➔ SEU is 2 consecutive bits error in the byte word
- ➔ Functional error, maxtime erase/write

## Read only mode: Argon (14)

- ➔ Block 0 erased
- ➔ Functional error, max time erase/write, recover after Reset

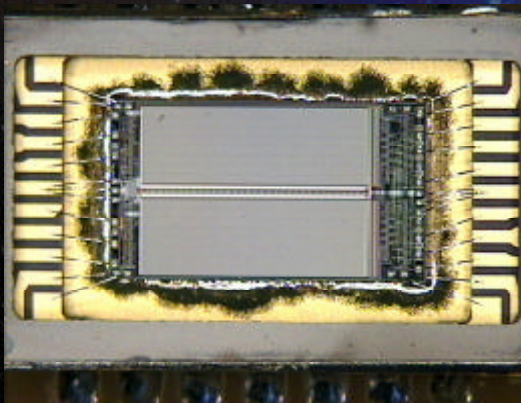
## Read / write mode: Neon (5.9)

- ➔ Block 0 erased
- ➔ Functional error, max time erase/write, recover after Reset
- ➔ Functional error, all blocks at 0, need to be powered off





# HM65687A TEMIC MHS



- CMOS Static RAM
- HM4-65687SB
- 22-Lead Rectangular LCC
- 64K x 1
- 5V operation
- 45 ns Access Time
- CMOS

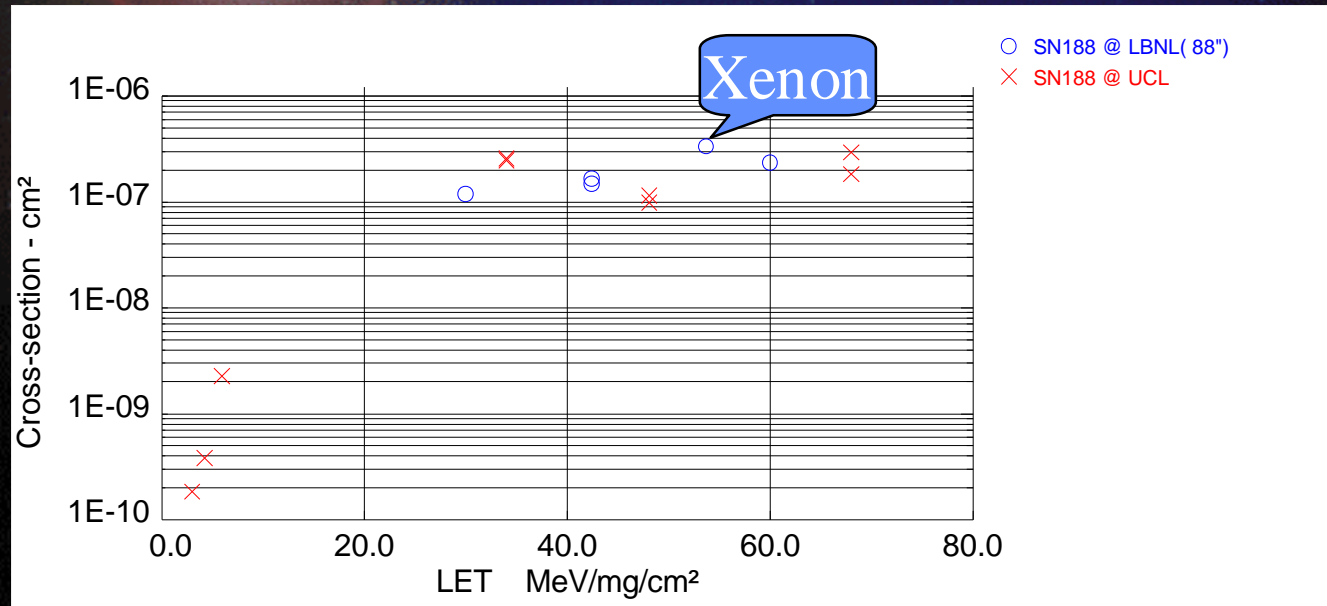


One hirel sample from Envisat programme





# HM65687A SEE RESULTS



UCL

8 4-Kr @ 316MeV

LBNL

86-Kr @ 886MeV

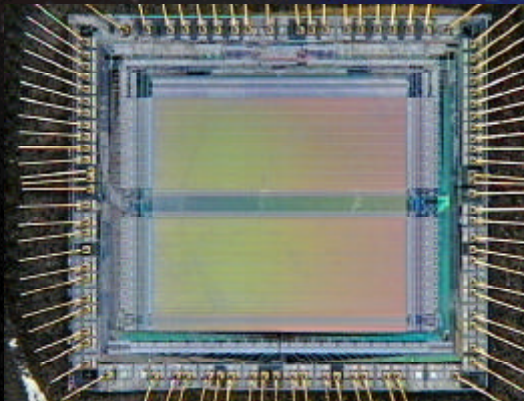
LET Threshold  $\sim 3 \text{ MeV}/(\text{mg}/\text{cm}^2)$

Asymptotic cross-section  $\sim 3 \text{ E} - 7 \text{ cm}^2$  per bit @  $68 \text{ MeV}/(\text{mg}/\text{cm}^2)$





# IDT7025 IDT



- Dual Port RAM
- IDT7025L35PFI
- 100-pin TQFP
- 8k x 16
- 5V operation
- 35 ns Read/Write Cycle Time
- CMOS
- Die : 4.8 mm x 5.4 mm

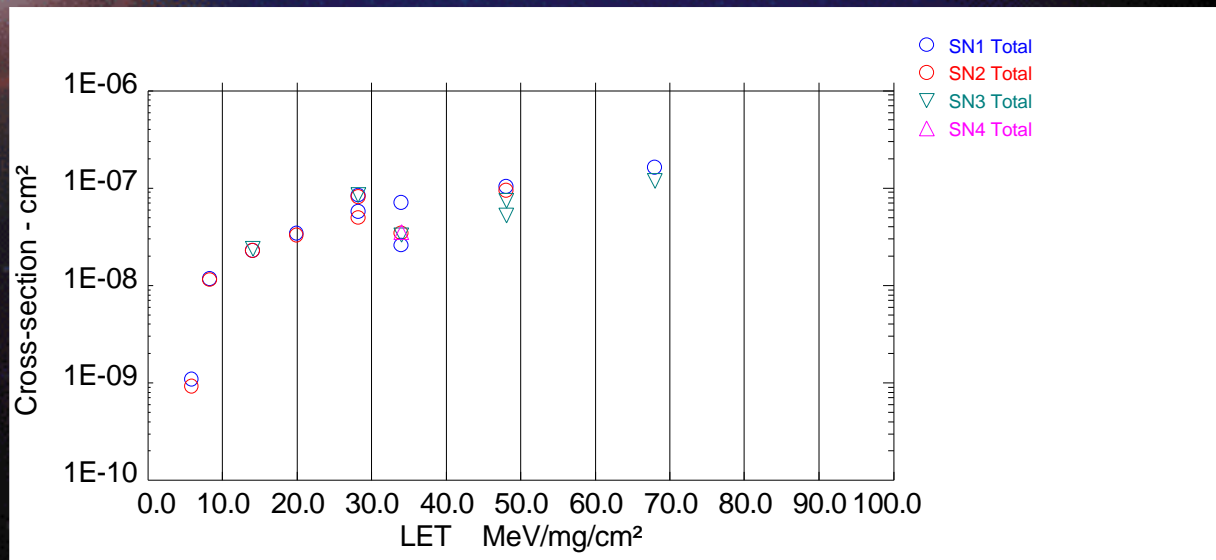


Only one port tested





# IDT7025 SEE RESULTS



- No SEL
- LET Threshold  $\sim 5.8 \text{ MeV}/(\text{mg}/\text{cm}^2)$
- Asymptotic cross-section  $\sim 1.2 \text{ E} - 7 \text{ cm}^2$  per bit @  $68 \text{ MeV}/(\text{mg}/\text{cm}^2)$
- 1st stuck bits Argon @ 60 deg.





# HX6228 HONEYWELL



- SRAM
- HX6228/TENC
- 32-lead Flatpack
- 128k x 8
- 5V operation
- 25ns Read/Write Cycle Time
- CMOS on SOI



Influence of temperature on SEE tolerance





# HX6228 SEE RESULTS

Ion 132-Xenon

Test temperature : ambient (27°C), 85 °C, 125 °C

Results

- At normal incidence, no error
- With a tilt angle of 60 deg., LET 112MeV/(mg/cm<sup>2</sup>)

Temperature (°C)	Fluence (p/cm <sup>2</sup> )	SEUs	Sigma per bit (cm <sup>2</sup> )
27	1.50 E +06	3	1.91 E -12
85	5.00 E +05	4	7.63 E -12
125	1.50 E +06	7	4.45 E -12